

2N5088

Rev.E Mar.-2016



DATA SHEET

TO-92

NPN

Silicon NPN transistor in a TO-92 Plastic Package.

Low noise, high gain.

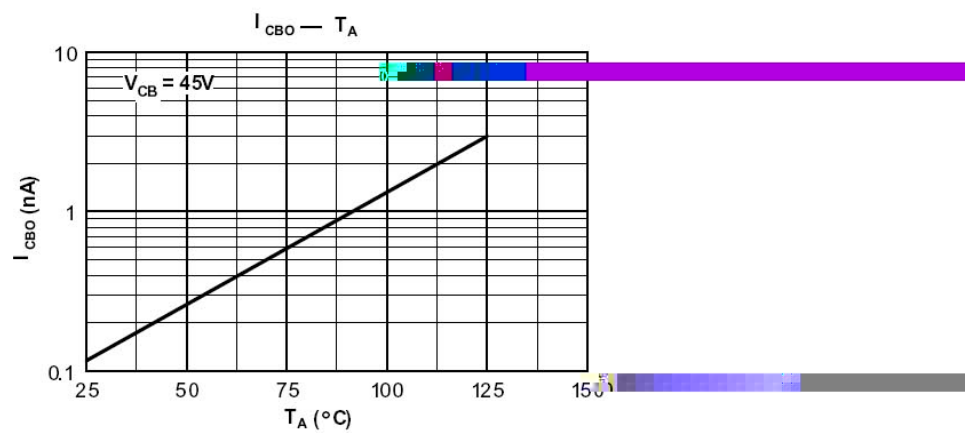
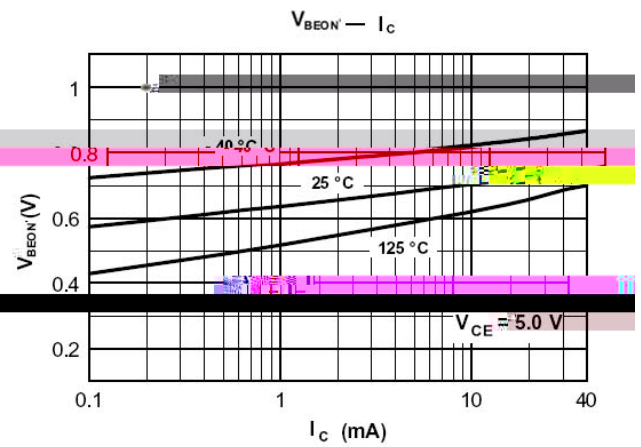
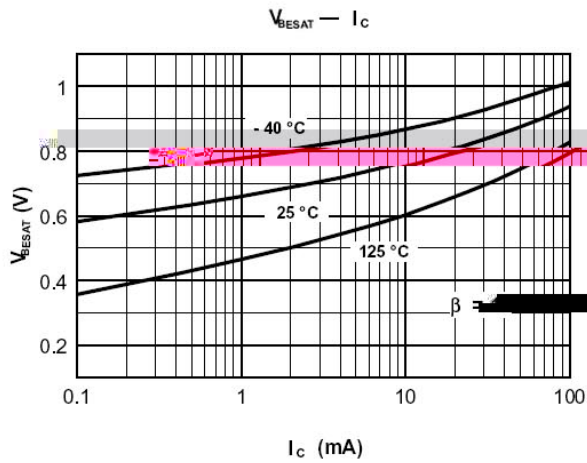
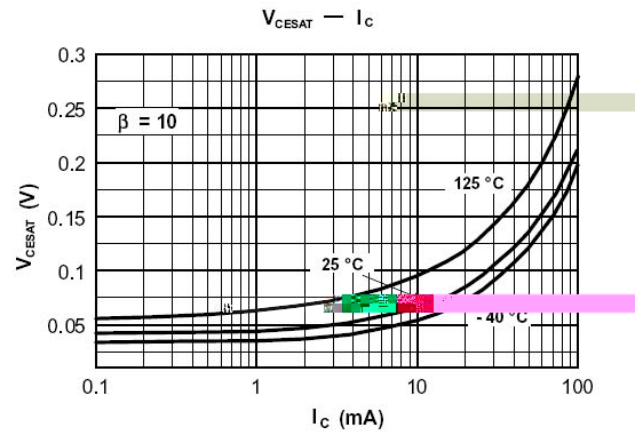
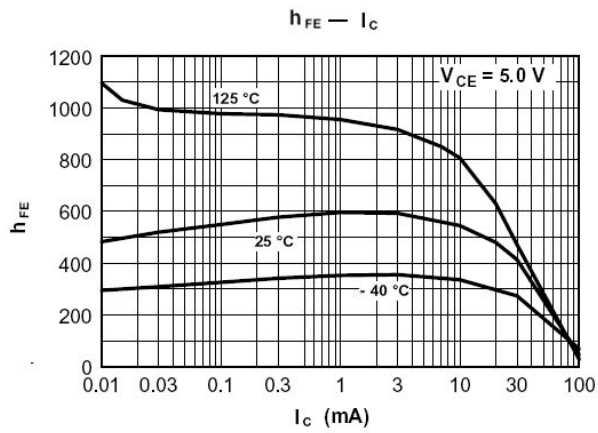
1uA 50uA

This device is designed for general purpose amplifier applications at collector currents from 1 A to 50

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	4.5	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=20V$ $I_E=0$			50	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=3V$ $I_C=0$			50	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V$ $I_C=100 A$	300	900		
	$h_{FE(2)}$	$V_{CE}=5V$ $I_C=10mA$	300			
	$h_{FE(3)}$	$V_{CE}=5V$ $I_C=1mA$	350			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1mA$			0.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	I_C				

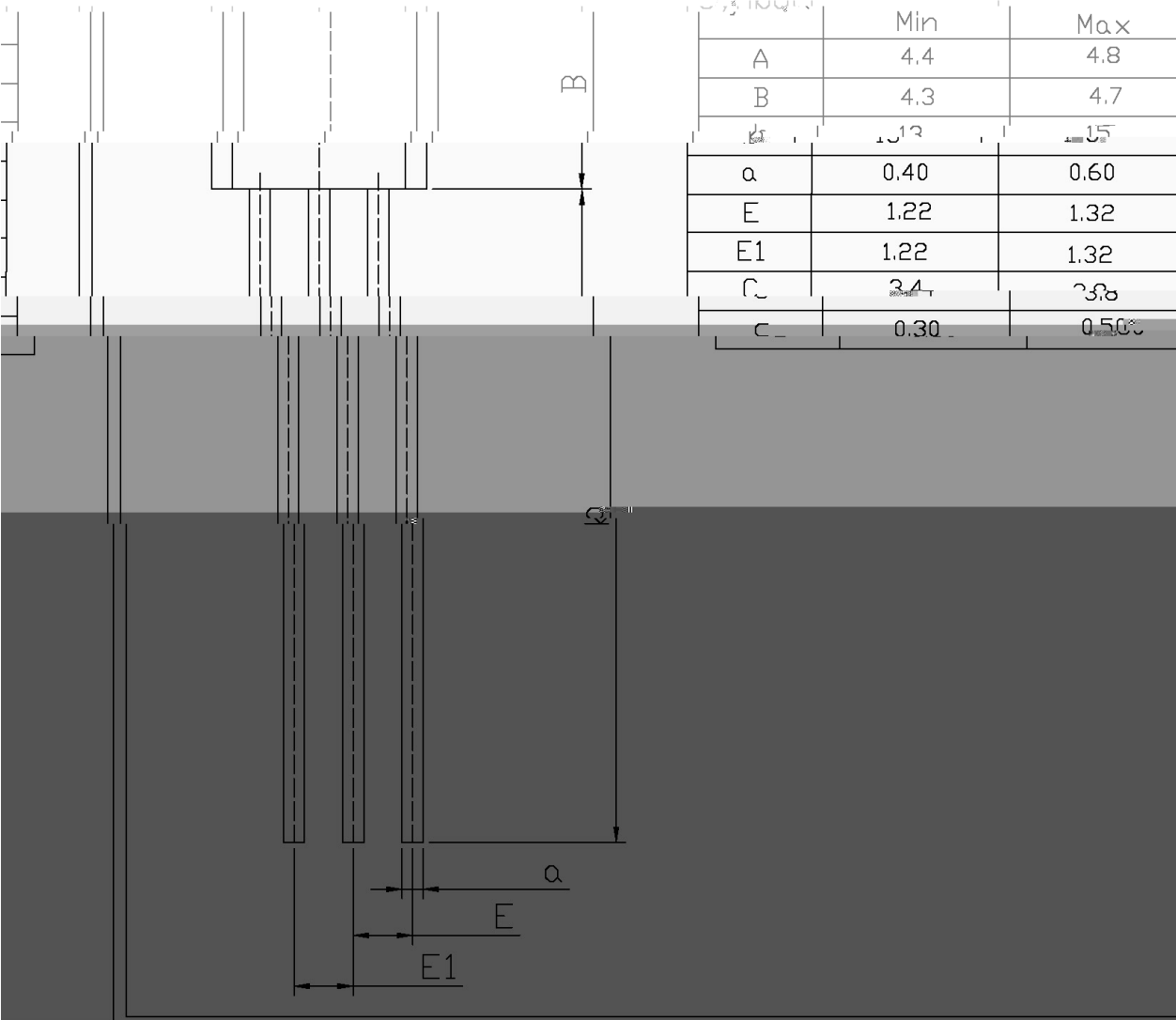
/ Electrical Characteristic Curve



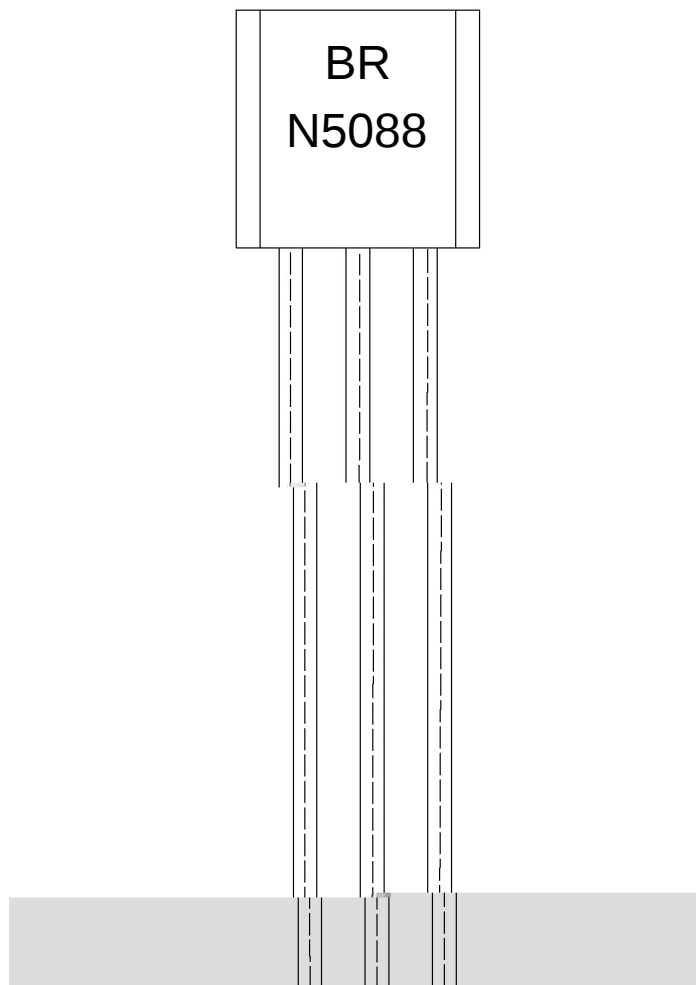
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



BR

N5088

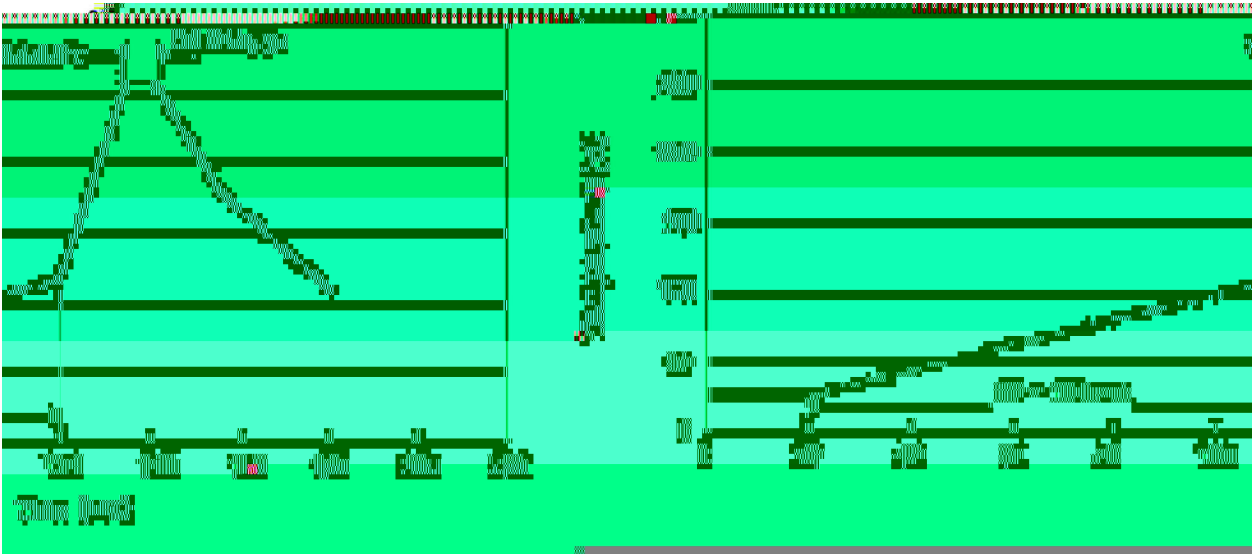
Note:

BR: Company Code.

N5088: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- Note:

1. Preheating: 25~150 , Time: 60~90sec.

2. Peak Temp.: 255±5 , Duration: 5±0.5sec.

3. Cooling Speed: 2~10 /sec.
- | | | | | |
|---|-------|-----|-----------|--------|
| 1 | 25 | 150 | 60 | 90sec; |
| 2 | 255±5 | | 5±0.5sec; | |
| 3 | | 2 | 10 | /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5